

AN: PAT 1997-463782

TI: Organic metal wafer growth of aluminium gallium arsenide
thin film for laser diode involves adding indium on crystalline
face after interrupting the growth of aluminium-gallium-arsenic
barrier layer

PN: JP09214052-A

PD: 15.08.1997

AB: The growth involves growing thin film crystal containing
one layer or multilayer AlGaAs barrier layer (3) on GaAs
substrate (1). Thus, epitaxial crystal for laser diode is
produced. In the middle of growth of AlGaAs barrier layer, the
growth is interrupted and In is added on crystalline front face.
; Improved light emitting life of laser. Reduced crystal defect
generation.

PA: (HITD) HITACHI CABLE LTD;

FA: JP09214052-A 15.08.1997;

CO: JP;

IC: C23C-016/48; H01L-021/205; H01S-003/18;

MC: L04-A02A; L04-A02D; L04-E03B; U11-C01B; U11-C01J3A;

DC: L03; U11;

FN: 1997463782.gif

PR: JP0016252 01.02.1996;

FP: 15.08.1997

UP: 20.10.1997

